

Silicon N Channel MOS Type (U-MOSⅢ)/Silicon Epitaxial Schottky Barrier Diode

SSM5H12TU

DC-DC Converter Applications

- 1.8-V drive
- Combined an N-ch MOSFET and a Schottky barrier diode in one package.
- Low $R_{DS(ON)}$ and Low V_F

Absolute Maximum Ratings

MOSFET ($T_a = 25^\circ\text{C}$)

Characteristic		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	30	V
Gate-source voltage		V_{GSS}	± 12	V
Drain current	DC	I_D	1.9	A
	Pulse	I_{DP}	3.8	
Power dissipation		P_D (Note 1)	0.5	W
		$t = 10\text{s}$	0.8	
Channel temperature		T_{ch}	150	$^\circ\text{C}$

Schottky Barrier Diode ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Repetitive peak reverse voltage	V_{RRM}	30	V
Average forward current	$I_{F(AV)}$	0.7	A
Peak one cycle surge forward current	I_{FSM}	2 (50Hz)	A
Junction temperature	T_j	125	$^\circ\text{C}$

MOSFET and Diode ($T_a = 25^\circ\text{C}$)

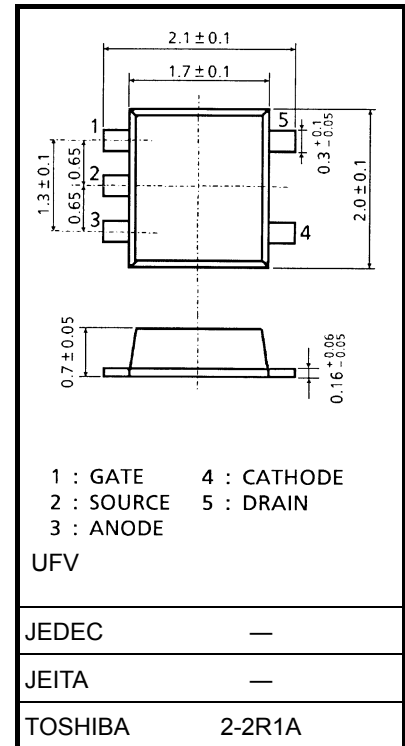
Characteristics	Symbol	Rating	Unit
Storage temperature range	T_{stg}	-55 to 125	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

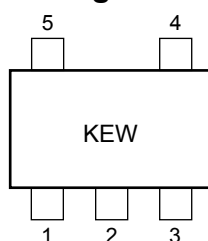
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Note 1: Mounted on FR4 board
(25.4 mm × 25.4 mm × 1.6 mm, Cu pad: 645 mm²)

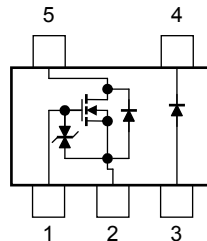
Unit: mm



Marking



Equivalent Circuit (top view)



MOSFET

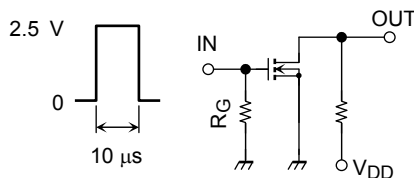
Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Conditions	Min	Typ.	Max	Unit
Drain-source breakdown voltage	$V_{(BR)DSS}$	$I_D = 1 \text{ mA}$, $V_{GS} = 0 \text{ V}$	30	—	—	V
	$V_{(BR)DSX}$	$I_D = 1 \text{ mA}$, $V_{GS} = -12 \text{ V}$	18	—	—	
Drain cut-off current	I_{DSS}	$V_{DS} = 30 \text{ V}$, $V_{GS} = 0 \text{ V}$	—	—	1	μA
Gate leakage current	I_{GSS}	$V_{GS} = \pm 12 \text{ V}$, $V_{DS} = 0 \text{ V}$	—	—	± 1	μA
Gate threshold voltage	V_{th}	$V_{DS} = 3 \text{ V}$, $I_D = 1 \text{ mA}$	0.4	—	1.0	V
Forward transfer admittance	$ Y_{fs} $	$V_{DS} = 3 \text{ V}$, $I_D = 1.0 \text{ A}$ (Note 2)	2.0	3.9	—	S
Drain-source ON-resistance	$R_{DS(ON)}$	$I_D = 1.0 \text{ A}$, $V_{GS} = 4.0 \text{ V}$ (Note 2)	—	103	133	$\text{m}\Omega$
		$I_D = 0.8 \text{ A}$, $V_{GS} = 2.5 \text{ V}$ (Note 2)	—	125	177	
		$I_D = 0.5 \text{ A}$, $V_{GS} = 1.8 \text{ V}$ (Note 2)	—	165	296	
Input capacitance	C_{iss}	$V_{DS} = 15 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 1 \text{ MHz}$	—	123	—	pF
Output capacitance	C_{oss}		—	43	—	
Reverse transfer capacitance	C_{rss}		—	18	—	
Total gate charge	Q_g	$V_{DS} = 15 \text{ V}$, $I_D = 1.9 \text{ A}$ $V_{GS} = 4 \text{ V}$	—	1.9	—	nC
Gate-source charge	Q_{gs}		—	1.1	—	
Gate-drain charge	Q_{gd}		—	0.8	—	
Switching time	Turn-on time	$V_{DD} = 15 \text{ V}$, $I_D = 1.0 \text{ A}$, $V_{GS} = 0 \text{ to } 2.5 \text{ V}$, $R_G = 4.7 \Omega$	—	9.2	—	ns
	Turn-off time		—	6.4	—	
Drain-source forward voltage	V_{DSF}	$I_D = -1.9 \text{ A}$, $V_{GS} = 0 \text{ V}$ (Note 2)	—	-0.83	-1.2	V

Note 2: Pulse test

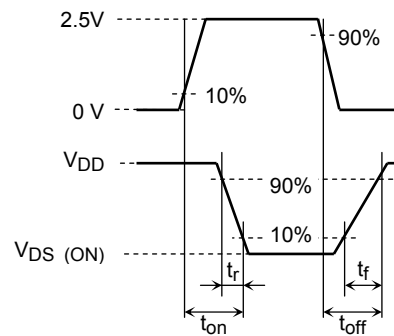
Switching Time Test Circuit

(a) Test Circuit

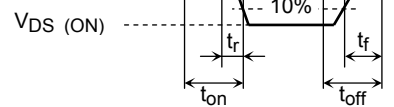


$V_{DD} = 15 \text{ V}$
 $R_G = 4.7 \Omega$
 Duty $\leq 1\%$
 V_{IN} : $t_r, t_f < 5 \text{ ns}$
 Common Source
 $T_a = 25^\circ\text{C}$

(b) V_{IN}



(c) V_{OUT}



Precaution

V_{th} can be expressed as voltage between gate and source when the low operating current value is $I_D = 1 \text{ mA}$ for this product. For normal switching operation, $V_{GS(ON)}$ requires a higher voltage than V_{th} and $V_{GS(OFF)}$ requires a lower voltage than V_{th} .

(The relationship can be established as follows: $V_{GS(OFF)} < V_{th} < V_{GS(ON)}$)

Be sure to take this into consideration when using the device.

Schottky Barrier Diode

Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Peak forward voltage	V _{FM} (1)	I _F = 0.5 A	—	0.34	0.41	V
	V _{FM} (2)	I _F = 0.7 A	—	0.37	0.44	V
Repetitive peak reverse current	I _{RRM}	V _R = 15 V	—	60	200	μA
Total capacitance	C _T	V _R = 0 V, f = 1 MHz	—	139	—	pF

Precaution

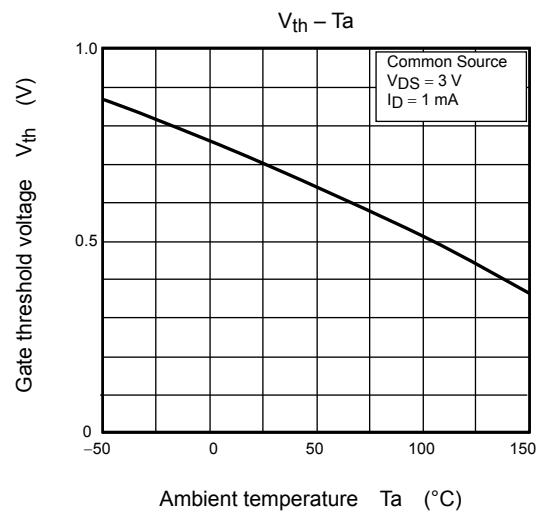
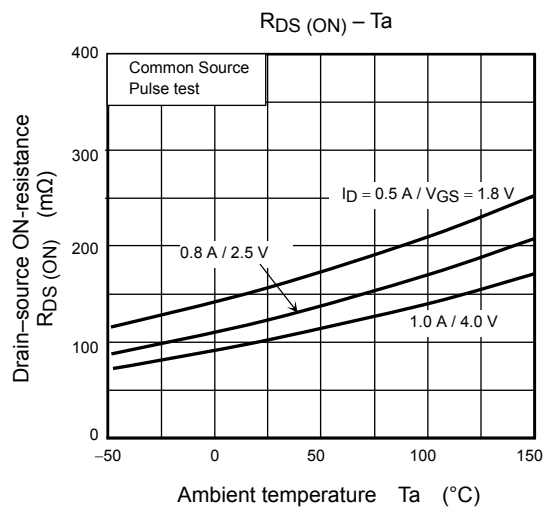
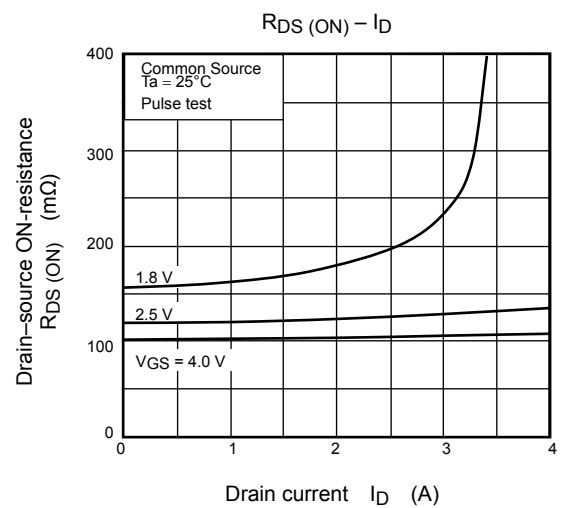
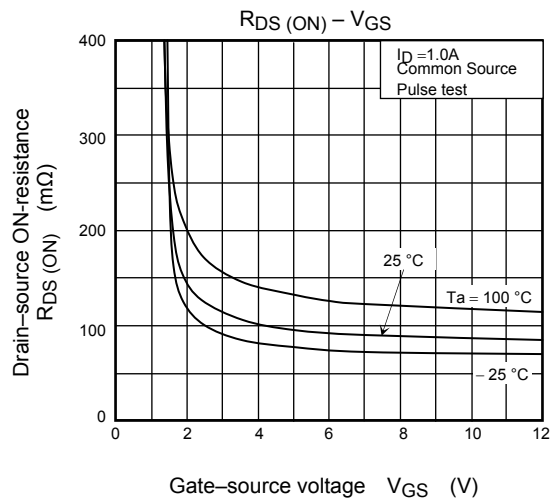
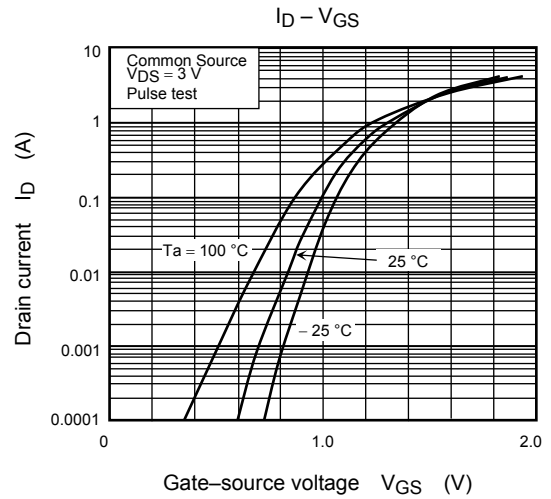
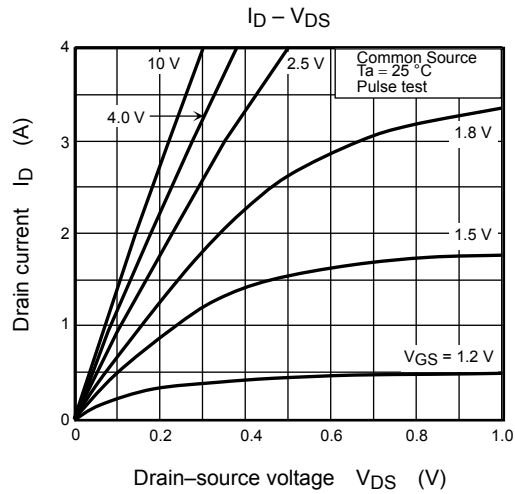
The Schottky barrier diode in this device has large reverse current leakage compared to typical switching diodes. Thus, excessive operating temperature or voltage may cause thermal runaway. To avoid this problem, be sure to take both forward and reverse loss into consideration.

Handling Precaution

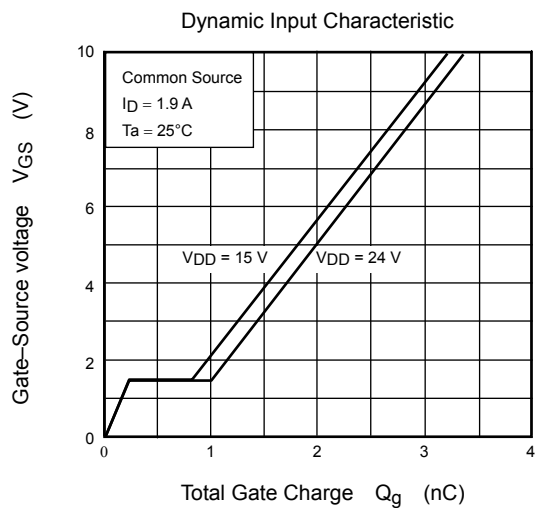
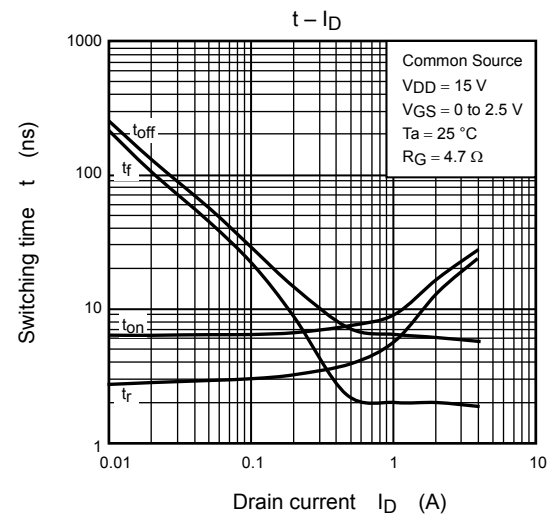
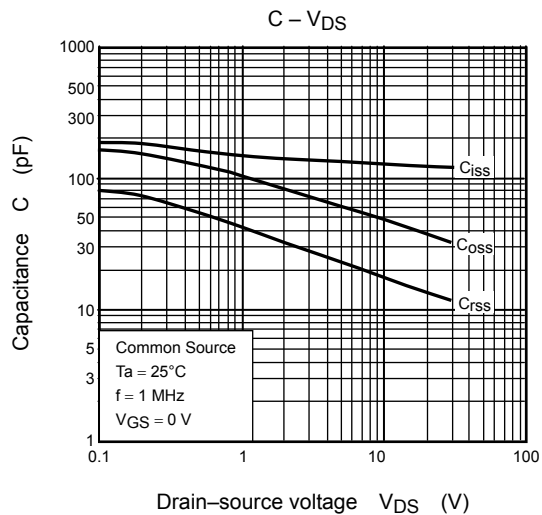
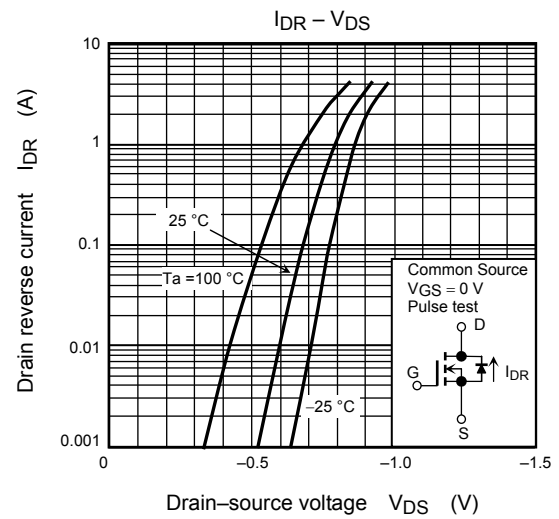
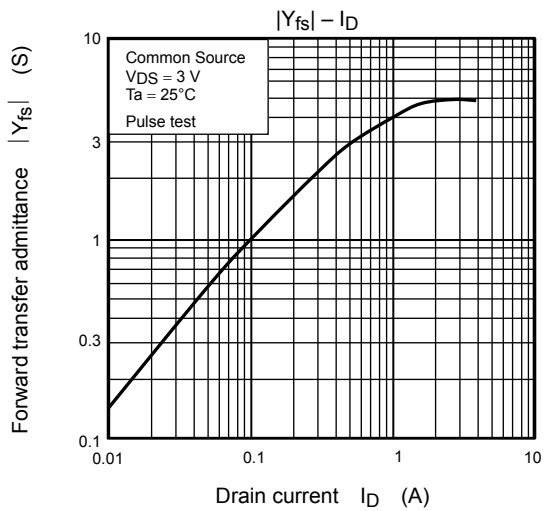
When handling individual devices (which are not yet mounted on a circuit board), ensure that the environment is protected against static electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

Thermal resistance R_{th(j-a)} and power dissipation P_D vary depending on board material, board area, board thickness and pad area. When using this device, please take heat dissipation into consideration.

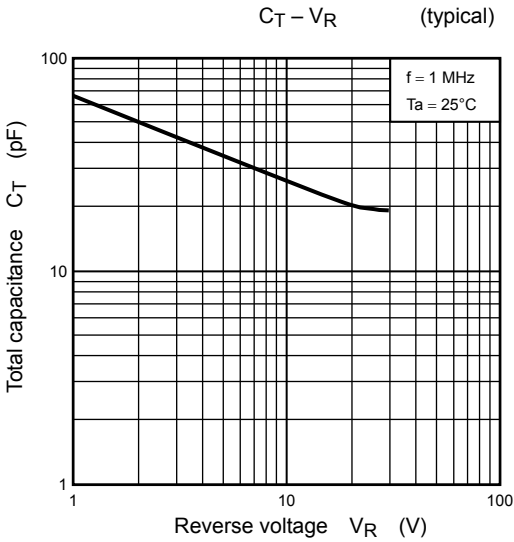
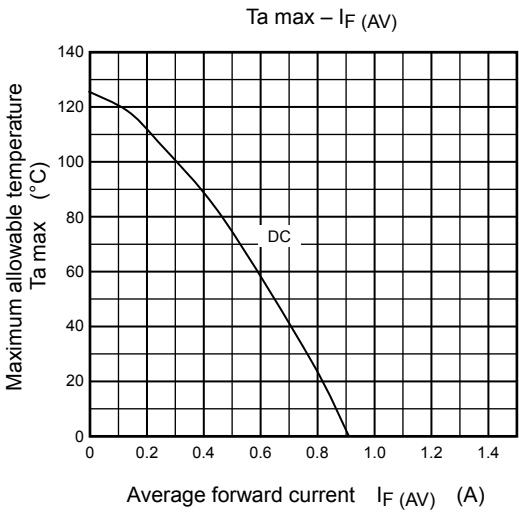
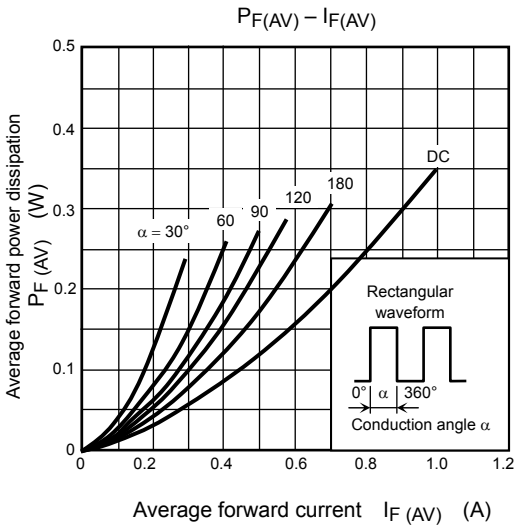
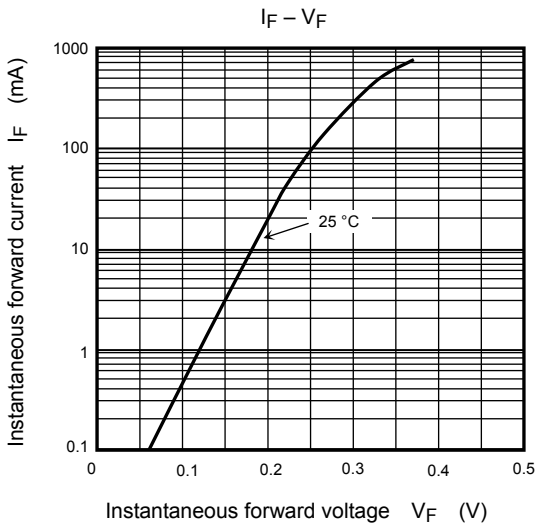
MOSFET



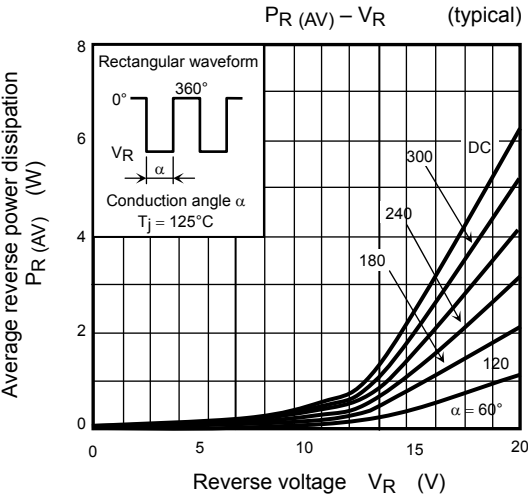
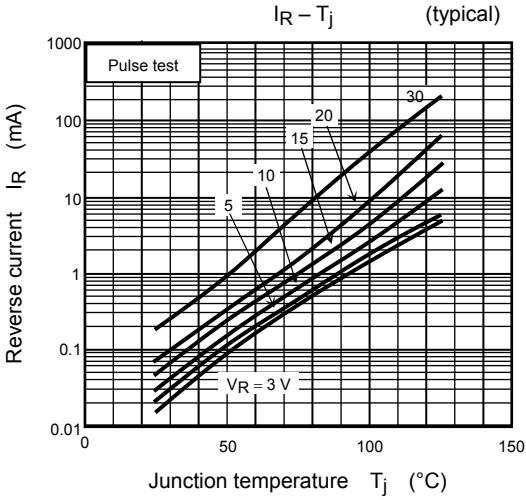
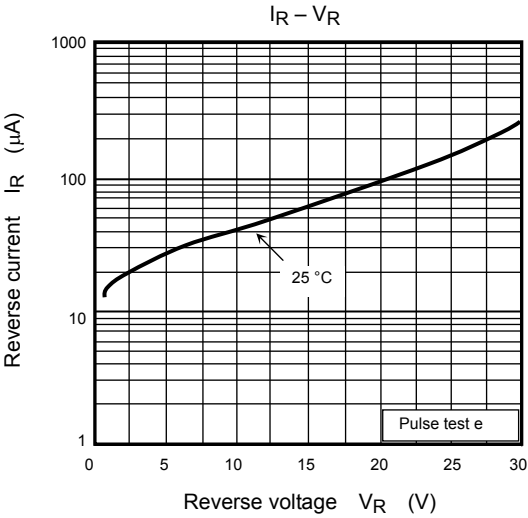
MOSFET



Schottky Barrier Diode



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